

2SK2126

Silicon N-Channel Power F-MOS FET

■ Features

- Avalanche energy capacity guaranteed: $EAS > 100\text{mJ}$
- $V_{GSS} = \pm 30\text{V}$ guaranteed
- High-speed switching: $t_f = 40\text{ns}$
- No secondary breakdown

■ Applications

- Contactless relay
- Diving circuit for a solenoid
- Driving circuit for a motor
- Control equipment
- Switching power supply

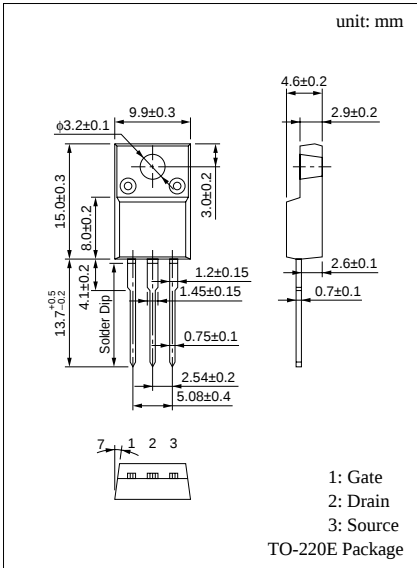
■ Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$)

Parameter		Symbol	Ratings	Unit
Drain to Source breakdown voltage		V_{DSS}	500	V
Gate to Source voltage		V_{GSS}	± 30	V
Drain current	DC	I_D	± 5	A
	Pulse	I_{DP}	± 10	A
Avalanche energy capacity		EAS^*	100	mJ
Allowable power dissipation	$T_C = 25^\circ\text{C}$	P_D	50	W
	$T_a = 25^\circ\text{C}$		2	
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature		T_{stg}	-55 to $+150$	$^\circ\text{C}$

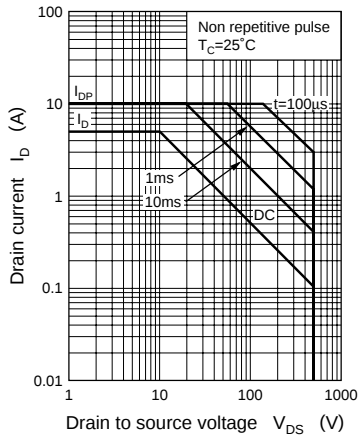
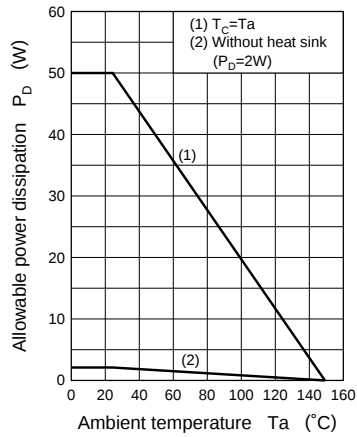
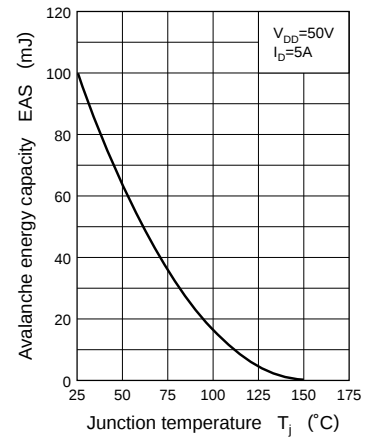
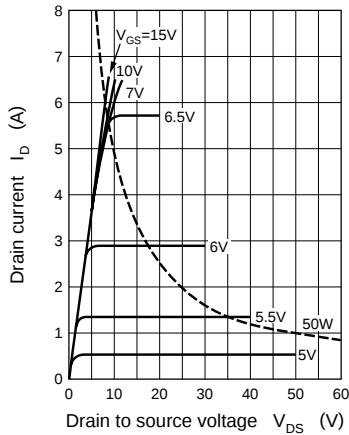
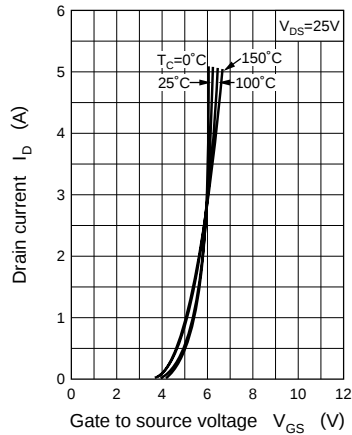
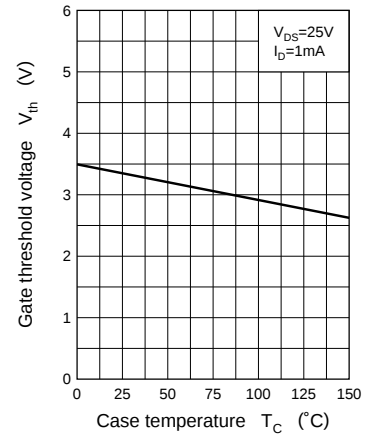
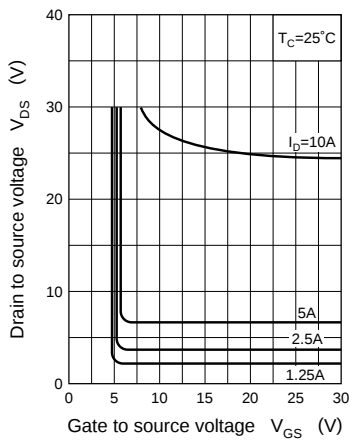
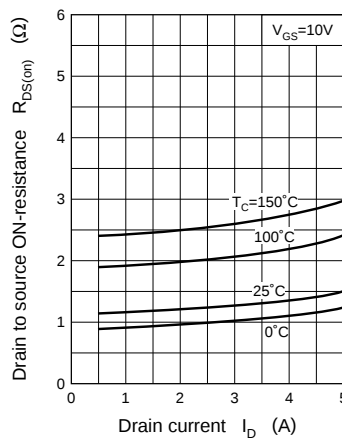
* $L = 8\text{mH}$, $I_L = 5\text{A}$, $V_{DD} = 50\text{V}$, 1 pulse

■ Electrical Characteristics ($T_C = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	I_{DSS}	$V_{DS} = 400\text{V}$, $V_{GS} = 0$			0.1	mA
Gate to Source leakage current	I_{GSS}	$V_{GS} = \pm 30\text{V}$, $V_{DS} = 0$			± 1	μA
Drain to Source breakdown voltage	V_{DSS}	$I_D = 1\text{mA}$, $V_{GS} = 0$	500			V
Gate threshold voltage	V_{th}	$V_{DS} = 25\text{V}$, $I_D = 1\text{mA}$	2		5	V
Drain to Source ON-resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}$, $I_D = 3\text{A}$		1.35	1.7	Ω
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 25\text{V}$, $I_D = 3\text{A}$	2	3.5		S
Diode forward voltage	V_{DSF}	$I_{DR} = 5\text{A}$, $V_{GS} = 0$			-1.6	V
Input capacitance (Common Source)	C_{iss}	$V_{DS} = 20\text{V}$, $V_{GS} = 0$, $f = 1\text{MHz}$		700		pF
Output capacitance (Common Source)	C_{oss}			100		pF
Reverse transfer capacitance (Common Source)	C_{rss}			35		pF
Turn-on time (delay time)	$t_{d(on)}$	$V_{GS} = 10\text{V}$, $I_D = 3\text{A}$ $V_{DD} = 150\text{V}$, $R_L = 50\Omega$		20		ns
Rise time	t_r			40		ns
Fall time	t_f			40		ns
Turn-off time (delay time)	$t_{d(off)}$			80		ns
Thermal resistance between channel and case	$R_{th(ch-c)}$				2.5	$^\circ\text{C/W}$



Area of safe operation (ASO)

 $P_D - T_a$ EAS — T_j  $I_D - V_{DS}$  $I_D - V_{GS}$  $V_{th} - T_C$  $V_{DS} - V_{GS}$  $R_{DS(on)} - I_D$  $|Y_{fs}| - I_D$ 